



JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

TO-92 Plastic-Encapsulate Transistors

A92 TRANSISTOR (PNP)

FEATURES

Power dissipation

P_{CM} : 0.625W ($T_{amb}=25$)

Collector current

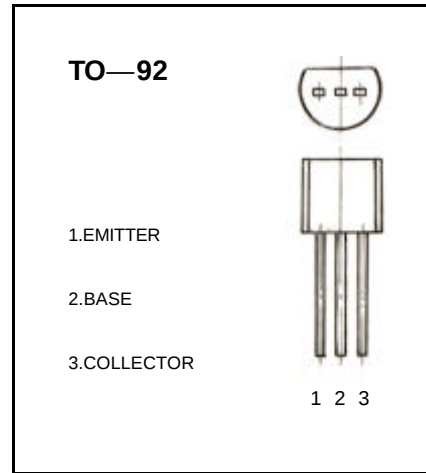
I_{CM} : -0.5 A

Collector-base voltage

$V_{(BR)CBO}$: -300V

Operating and storage junction temperature range

T_J , T_{stg} : -55 to +150



ELECTRICAL CHARACTERISTICS ($T_{amb}=25$ unless otherwise specified)

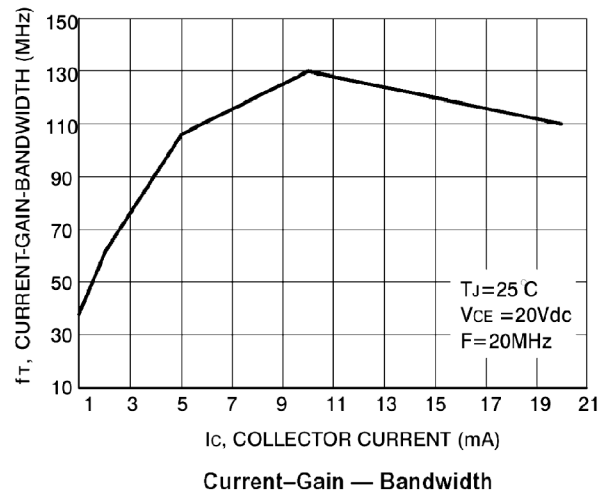
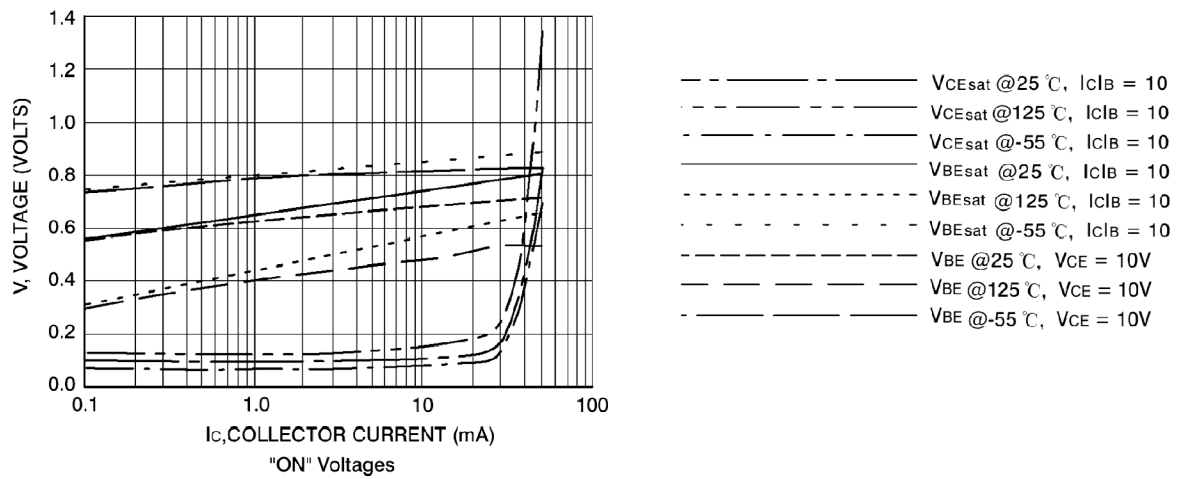
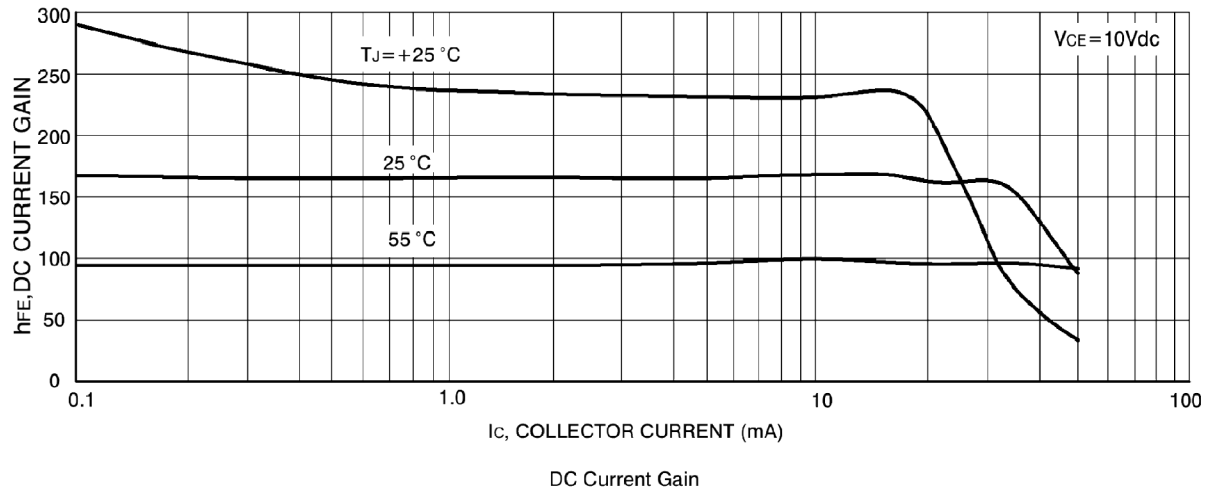
Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -100 \mu A$, $I_E = 0$	-300			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -1 mA$, $I_B = 0$	-300			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -100 \mu A$, $I_C = 0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB} = -200 V$, $I_E = 0$			-0.25	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -5 V$, $I_C = 0$			-0.1	μA
DC current gain	$h_{FE(1)}$	$V_{CE} = -10 V$, $I_C = -1 mA$	60			
	$h_{FE(2)}$	$V_{CE} = -10 V$, $I_C = -10 mA$	80		250	
	$h_{FE(3)}$	$V_{CE} = -10 V$, $I_C = -80 mA$	60			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -20 mA$, $I_B = -2 mA$			-0.2	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = -20 mA$, $I_B = -2 mA$			-0.9	V
Transition frequency	f_T	$V_{CE} = -20 V$, $I_C = -10 mA$ $f = 30 MHz$	50			MHz

CLASSIFICATION OF $h_{FE(2)}$

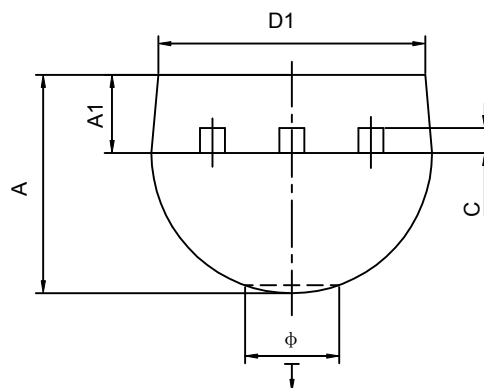
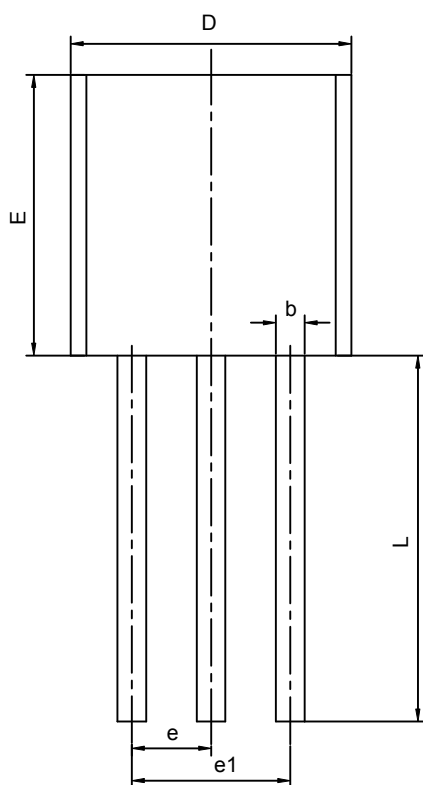
Rank	A	B ₁	B ₂	C
Range	80-100	100-150	150-200	200-250

Typical Characteristics

A92



TO-92 PACKAGE OUTLINE DIMENSIONS



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	3.300	3.700	0.130	0.146
A1	1.100	1.400	0.043	0.055
b	0.380	0.550	0.015	0.022
c	0.360	0.510	0.014	0.020
D	4.400	4.700	0.173	0.185
D1	3.430		0.135	
E	4.300	4.700	0.169	0.185
e	1.270TYP		0.050TYP	
e1	2.440	2.640	0.096	0.104
L	14.100	14.500	0.555	0.571
Ö		1.600		0.063
$\downarrow$	0.000	0.380	0.000	0.015